EAST WEST UNIVERSITY DEPT. OF EEE

SECTION: 01

COURSE CODE: EEE 416

COURSE NAME: VLSI GREWITS & SYSTEM

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LAB REPORT 04

EXPERIMENT NAME: NOR 2 INPUT SCHEMATIC, SYMBOL & LAYOUT GENERATION

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Objective: The objective is to design a NOR gate with two inputs, including creating a schematic, symbol and layout for Jabrication. The schematic will illustrate the cincuitry. The sysbol will represent it in diagrams, and the layout will depict physical placement of component on a chip. This process ensure accurate representation & functionality of the NOR gate in electronic system.

Introduction: A schematic diagram shows the function of a cinquit with little emphasis on its physical characteristics. The primary goal of the sheematic diagram it to show the functional relationships between components like MOSFETS, allowing the cinquit to be easily analysed. Schematics for electrolic cinquits love prepared by designers using EDA tools such as Schematic XL to Vintuoso from Cadence.

Methodology: To generate a NOR two inpuls schematic, symbol & layout, begin by using Electronic Design Automation (EDA) software UKO Cadence Vintuoso Design Compiler.

-> We will drag and drop NOR gates from the component library onto the schematic canvas. We will connect the inputs & outputs of the NOR gates using wines on buses, ansuring correct logic component.

-> We will generate a symbol for the NOR gate by armanging standard logic sysbols for inpuls & outputs in a way that clearly represents the gate's function. Ensure consistency with industry standards for symbol respresentation.

→ We will translate the schematic into a layout by placing transists & interconnects according to the design rules of the frabrication process.

Throny: A NOR gate is a digital logic gate that performs NOR operation. It has two on more inpuls & one output Eignals. The output of NOR gate is "high" only when none of its inpuls wa high". In other words, the output is "low" if any of the inputs over high. The NOR gote is chancelinized by its Anuth table, which shows the notationship between its inputs and output. It is widely used in digital electionics for vacious applications such as Boolean rogic operations, digital circuit design & building more complex logic functions.

Touth Table:

Α	B	Output
0	0	1
0	1	D
1	0	0
1	1	0

Specifications: -> Vac = 1.8V [DC VoHage]

-> Vpulse 1: Voltage = DV

Voltage=1.8V

Pariod = 200 815

Pulse Width = 100 ms

| connected to "a"]

-> Vpulsaz: Voltogo = OV

Voltago = 1.8V [Connected to "b"]

Parriod = 100 ns

Pulsa Width = 50 ms

Process: Generating a NOR gate with two inputs typically severals steps, including designing the schematic, creating a symbol for the gate & bying out the psysical components on a chip on booked.

-> We will stoot by creating a solumatic diagram using a CAD tool like Cadence. On CAD, Altium Designer on KiCad. We'll place two inputs nodes & one output nodes. We'll connect the inputs to the gate logic & connect the output to the appropriate gate.

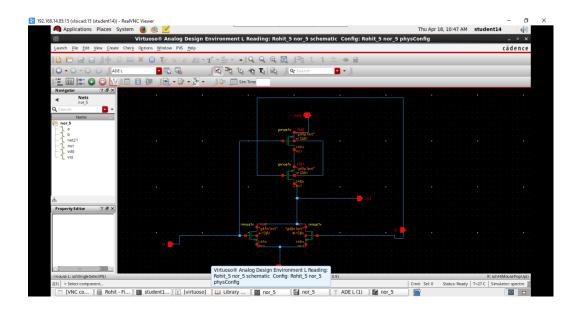
-> Woll design a graphically symbol to represent the NGR gate in circuit diagrams. This symbol typically consists of a triangle with a bubble at the output, respresentation the logical regation. The symbol should be easily necognizable components standard conventions.

- will layout the physical components of the NOR gate on a chip. Well define the placement & nouting of transistors, pesistors & other components according the schematic design. We'll ensure propon spacing & nouting to minimize signal interface and optimize penformace. & pay attention to factors like power consumption, signal propagation delay & noise immunity.

→ We'll vorify the connectness of the solumatic, symbol, layout by Simulating the behaviour of the NOR gate using specialized CAD tools. Wo'll test the gate in both & real world conditions to ensure it openals as expected. We'll itere on the design as necessary to address any issues on optimize performance.

→ We'll fabricate the NOR gate according to the finalized design files. We'll integrale the gate into larger systems or circuits as needed. Wo'll be performed quality assurance checks to perify that the manufactured gates meet the specified requirements.

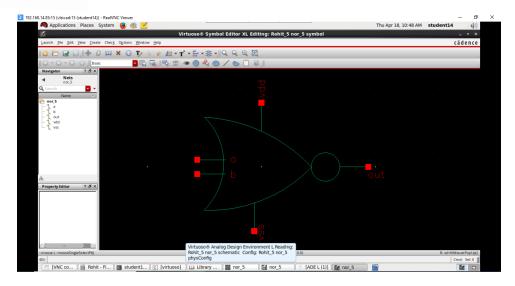
Schematic Draw NORX2



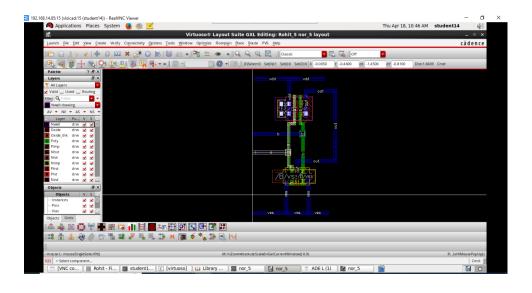
Signal Output



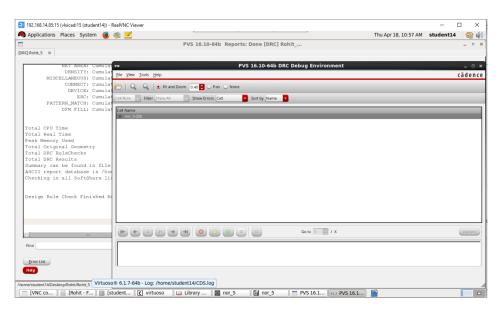
Symbol Draw



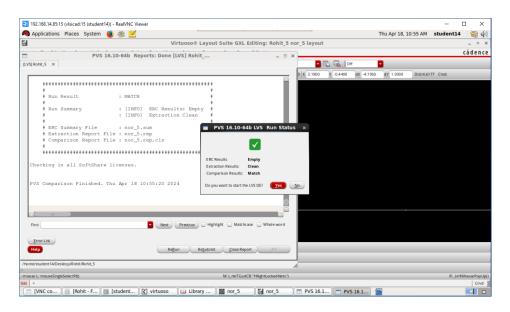
Layout







LVS RUN



Description of the passible process steps of this 45 nm NMOS device using the layers of the obtained layout individually in a sequential manner.

To elucidate the process steps involved in Jabrication a 45nm NMOS device, it typically begins with substrate preparation, followed by a series of sequencial processes meticulously executed on individual byers obtained from the layer. The substrate undergoes cleaning & primming steps to ensure uniformly & purity. Next, the gate oxide layer is deposited a patterned to define the transistor's channel region. Subsequently the polysilicon layer is deposited & patterned to form the gate electrode. Dopant ions are implaned into the silicon substrate to create the source & drain regions. A dielectric lower is then deposited & etched to create contact openings for source, drain & galt electrodes. Metal layers are deposited & patterned to form interconnects, connecting various components of the NMOS device. Finally, a possivation layers is deposited to protect the device from external environmental factors. Each of these sequential steps. meticulously executed on individual layers derived from the layout, contributes to the precise fabrication of the 45 nm NMOS device, ensuring its functionality & penformance

comments about the 45Nm technology: The 45nm technology represents a significant milestone in semiconductor Jabrication. characterized by its miniaturization. & enhanced performance capabilities, by shrinking the transistors size to 45nm, manufacturing achieve greater transistor density, enabling more functionality on a single thip while consuming less power. This technology facilitates the production of Jastor, more energy efficient electronic devices including processors

chips & integrated circuits, driving advantage in computing, communication & consumer electronics industries. The 45nm technology, has paved the way for further innovation & development in semi-conductor manufacturing, serving as a foundation for further generation of even smaller & more powerful electronic devices.

Discussion: The process of generating a Ner gote with two inputs involves several key steps: first, creating a schumotic diagram that outlines the logical connections between the inputs & the outputs. Next, a symbolic representation of the Nor gote is designed, typically featuring a triangle with a bubble at the output to denote the design. The physical layout of the gote is then generated, considering factors such as component placement, signal nexting & optimization for preformace metrics like power consumption & signal integrity. This layout is verified through simulation & testing to ensure functionality & adherence to design specification. Collaboration & adherence to standards one caucial throughout the process, from initial design to final babication & assembly, to ensure the successful implementation of the Nor gote in electronic systems.

Conclusion: In conclusion, the process of generating a NoR gate with two inpuls involves designing a solumoitic responsenting the logical operation creating a symbol four easy responsentation in cincuit diagnam & laying out the physical components on a chip. This process requires meticulous attention to detail, adherence to design guildliness & through venification through simulation & testing. By following these steps, designers can create NOR gate that meet the required specifications & into larger systems.